























♦ Noise power ~ I_D & bandwidth

EEC247B/MEC218: Introduction to MEMS Design

Shot Noise * Associated with direct current flow in diodes and bipolar junction transistors Arises from the random nature by which e's and h's surmount the potential barrier at a pn junction The DC current in a forward-biased diode is composed of ht's from the pregion and e's from the n-region that pn-junction have sufficient energy to overcome the potential barrier at the junction → noise process should be proportional to DC current $=2qI_D$ • Attributes: ♥ Related to DC current over a barrier Charge on an e- □ Independent of temperature (=1.6×10-19C) ♦ White (i.e., const. w/ frequency)

DC Current

C. Nguyen















